

**FEATURES**

- Near Infrared Reduced Footprint Photodiode
- Photosensitive Active Area: 0.6 mm x 0.6 mm
- High Sensitivity: 0.65 A/W ( $\lambda = 850 \text{ nm}$ )
- Wide Operating Temperature: -40°C to +110°C
- Ideal for High Volume Laser Monitoring Applications
- RoHS and REACH Compliant

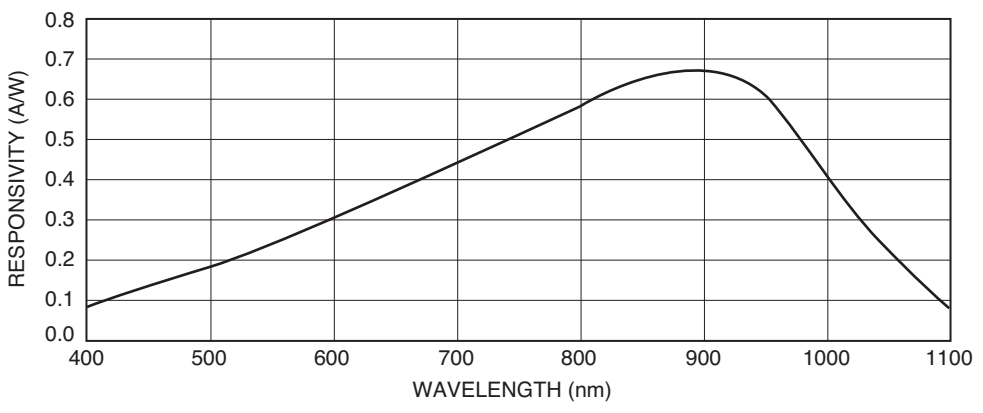
**Electro-Optical Characteristics at 25°C**

Parameters	Test Conditions	Min	Typ	Max	Units
Active Area			0.36		mm <sup>2</sup>
Responsivity	@ 850 nm		0.65		A/W
Dark Current, I <sub>dr</sub>	V <sub>r</sub> = 3 V		0.05	0.3	nA
Shunt Resistance	V <sub>R</sub> = 10 mV	200	1000		M $\Omega$
Reverse Breakdown Voltage, V <sub>R</sub>	I <sub>R</sub> = 10 $\mu$ A	25			Volts
Capacitance, C	V <sub>R</sub> = 0 V			8	pF
Rise Time	V <sub>R</sub> = 10 V		8	15	nsec

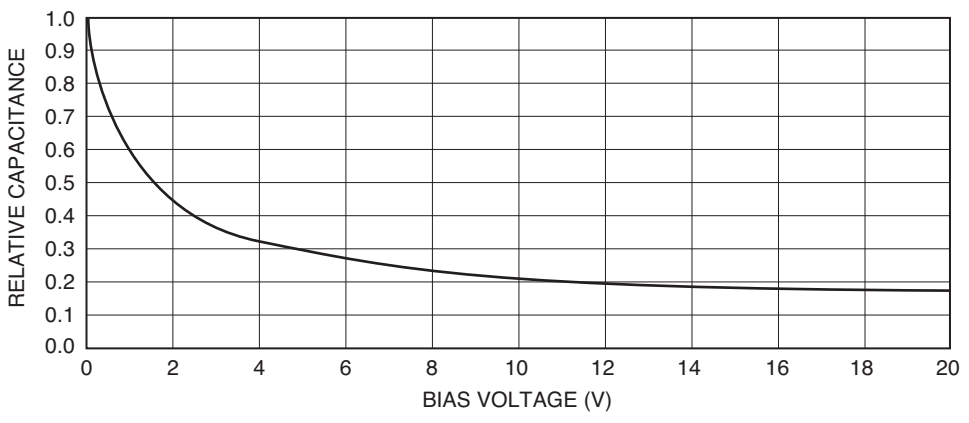
**Thermal Parameters**

Parameters	Units
Storage and Operating Temperature Range	-40°C to 110°C
Maximum Junction Temperature	110°C

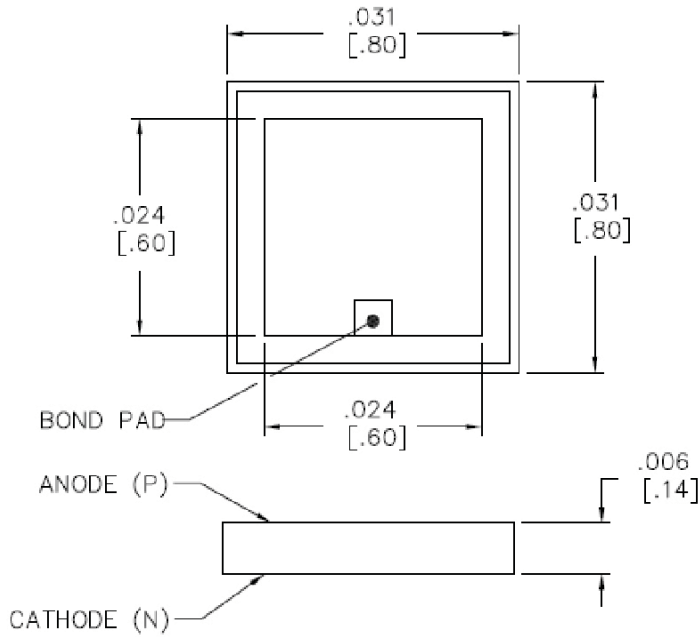
**Typical Spectral Response**



**Capacitance vs Bias Voltage**



Package Dimensions



Specifications are subject to change without prior notice.